

FGW50N60VD

Discrete IGBT

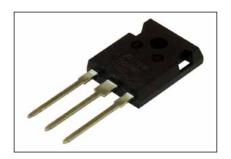
Discrete IGBT (High-Speed V series) 600V / 50A

■ Features

Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA, SCSOA etc.)

Applications

Inverter for Motor drive AC and DC Servo drive amplifier Uninterruptible power supply

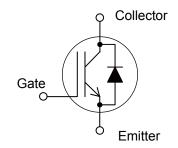


Equivalent circuit

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter voltage	Vces	600	V	
Gate-Emitter voltage	V _{GES}	±20	V	
DC Collector Current	Ic@25	85	Α	Tc=25°C, Tj=150°C
	Ic@100	50	Α	Tc=100°C, Tj=150°C
Pulsed Collector Current	I _{CP}	100	Α	Note *1
Turn-Off Safe Operating Area	-	100	Α	Vce≤600V, Tj≤175°C
Diode Forward Current	F@25	70	Α	
	F@100	35	Α	
Diode Pulsed Current	I _{FP}	100	Α	Note *1
Short Circuit Withstand Time	tsc	10	μs	Vcc≤320V, VgE=15V Tj≤150°C
IGBT Max. Power Dissipation	P _{D_IGBT}	360	W	Tc=25°C
FWD Max. Power Dissipation	P _{D_FWD}	220	VV	Tc=25°C
Operating Junction Temperature	T _i	-40~+175	°C	
Storage Temperature	T _{stg}	-55~+175	°C	



Note *1 : Pulse width limited by Tjmax.

● Electrical characteristics (at T_j= 25°C unless otherwise specified)

Itama	Symbols	Symbols Conditions			Characteristics			
Items	Symbols	Conditions	min.	typ.	max.	Unit		
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	$I_{C} = 250 \mu A, V_{GE} = 0 V$	600	-	-	V		
Zero Gate Voltage Collector Current	Ices	V _{CE} = 600V, V _{GE} = 0V	-	-	250	μA		
	ICES	I _j =1/5°C	-	-	10	mA		
Gate-Emitter Leakage Current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	200	nA		
Gate-Emitter Threshold Voltage	V _{GE (th)}	V _{CE} = +20V, I _C = 50mA	6.2	6.7	7.2	V		
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$V_{GE} = +15V, I_{C} = 50A$	-	1.60 2.1	2.05	V		
nput Capacitance	Cies	V _{CF} =25V	-	2900	-			
Output Capacitance	Coes	V _{GE} =0V	<u> </u>	215	_	pF		
Reverse Transfer Capacitance	Cres	f=1MHz	_	175	_	۲.		
toroico manoror capacitaneo	O les	V _{cc} = 400V		110				
Gate Charge	Q _G	Ic = 50A	_	360	-	nC		
3 -		V _{GE} = 15V						
Turn-On Delay Time	t _{d(on)}	T _j = 25°C	-	45	-			
Rise Time	t	V _{cc} = 400V	-	90	-			
Turn-Off Delay Time	t _{d(off)}	Ic = 50A	-	310	-	ns		
Fall Time	tr	V _{GE} = 15V	-	55	-			
Turn-On Energy	Eon	$R_G = 10\Omega$						
		L = 500µH			-	mJ		
Turn-Off Energy	Eoff	Energy loss include "tail" and FWD reverse	-	1.4				
		recovery.						
Turn-On Delay Time	t _{d(on)}	T _i = 175°C	_	45	-]		
Rise Time	t	Vcc = 400V	_	100	-	ns		
Turn-Off Delay Time	t _{d(off)}	Ic = 50A	_	340	-			
Fall Time	tr	V _{GE} = 15V	-	60	-			
Turn-On Energy	Eon	$R_G = 10\Omega$	-	4.1	-			
Turn-Off Energy		L = 500µH				mJ		
	Eoff	Energy loss include "tail" and FWD reverse	-	2.0	-			
		recovery.						
Forward Voltage Drop	VF	I ₌ =35A T _j =25°C	-	1.5	1.95	V		
		I _j =1/5°C	-	1.3	-	V		
Diada Davenas Basavany Tima		V _{cc} =30V			50 05			
Diode Reverse Recovery Time	t _{rr1}	I _F = 3.5A	-	50	65	ns		
Diode Reverse Recovery Time		-di/dt=200A/µs V _{cc} =400V			-			
Diode Neverse Recovery Tille	t _{rr2}	Vcc=400V I⊧=35A	-	0.31	-	μs		
		i⊧−35A -di⊧/dt=200A/μs						
Diode Reverse Recovery Charge	Qrr	-diε/dt-200A/μs Τ _i =25°C	-	0.75	-	μC		

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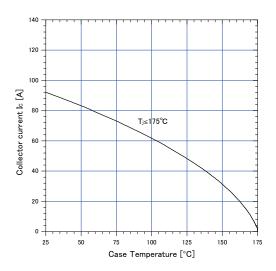
Items	Symbols Conditions		Characteristics			Unit
items	Symbols	Conditions	min.	typ.	max.	Unit
Diode Reverse Recovery Time	t _{rr2}	Vc=400V I⊧=35A	-	0.49	-	μs
Diode Reverse Recovery Charge	Qrr	-di⊧/dt=200A/μs T.=175°C	-	3.3	-	μC

● Thermal resistance

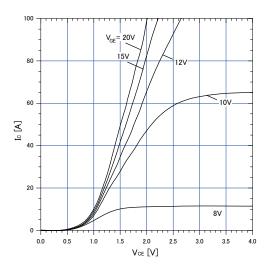
Items	Symbols		Unit		
	Symbols	min.	typ.	max.	Oilit
Thermal Resistance, Junction-Ambient	R _{th(j-a)}	-	-	50	
Thermal Resistance, IGBT Junction to Case	R _{th(j-c)_IGBT}	-	-	0.417	°C/W
Thermal Resistance, FWD Junction to Case	R _{th(j-c)_FWD}	-	-	0.735	

■ Characteristics (Representative)

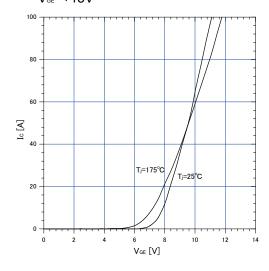
Graph.1 DC Collector Current vs T_c $V_{ce} \ge +15V$, $T_i \le 175$ °C



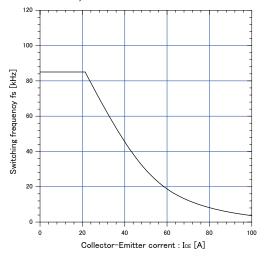
Graph.3 Typical Output Characteristics (V_{CE} - I_{C}) T_{J} =25°C



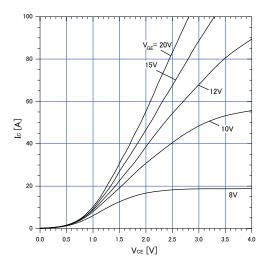
Graph.5 Typical Transfer Characteristics V_{GE} =+15V



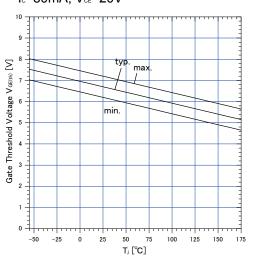
Graph.2 Collector Current vs. switching frequency V_{og} =+15V, T_{o} ≤175°C, V_{co} =400V, D=0.5, R_{o} =10 Ω , T_{o} =100°C



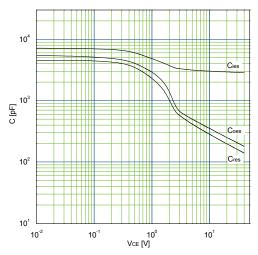
Graph.4
Typical Output Characteristics (V_{cE}-I_c)
T_i=175°C



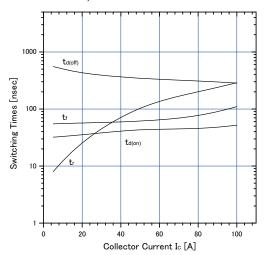
Graph.6
Gate Threshold Voltage vs. T_i
I_c=50mA, V_{cr}=20V



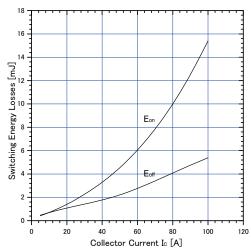
Graph.7 Typical Capacitance V_{s∈}=0V, f=1MHz, T_i=25°C



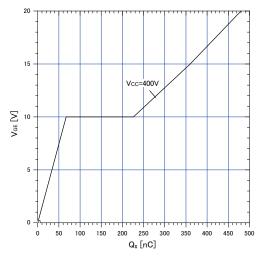
Graph.9 Typical switching time vs. I_c T_j =175°C, V_{cc} =400V, L=500 μ H V_{ce} =15V, R_c =10 Ω



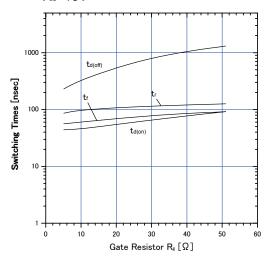
Graph.11 Typical switching losses vs. I_c T_i=175°C, V_{cc} =400V, L=500 μ H V_{ce} =15V, R_c =10 Ω



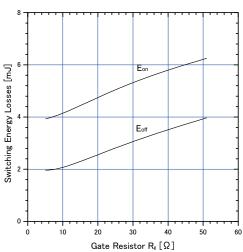
Graph.8 Typical Gate Charge V∞=400V, I₀=50A, T,=25°C



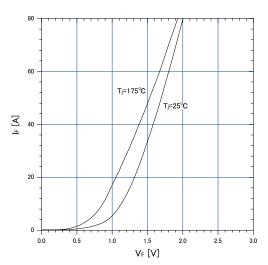
Graph.10 Typical switching time vs. $R_{\rm s}$ T₁=175°C, $V_{\rm cc}$ =400V, $I_{\rm c}$ =50A, L=500 μ H $V_{\rm ce}$ =15V



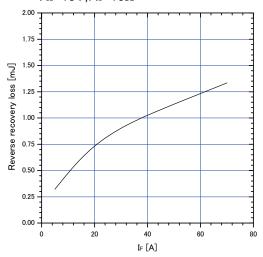
Graph.12 Typical switching losses vs. $R_{\rm G}$ T_J=175°C, V_{CC}=400V, I_C=50A, L=500 μ H V_{CE}=15V



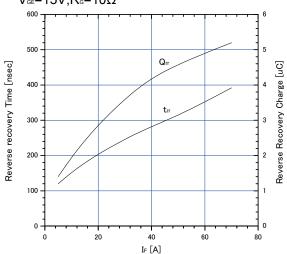
Graph.13 FWD Forward voltage drop (V_F-I_F)



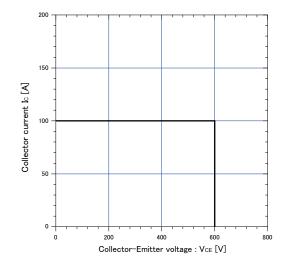
Graph.15 Typical reverse recovery loss vs. I_F T_i =175°C, V_{cc} =400V,L=500 μ H V_{ce} =15V, R_c =10 Ω



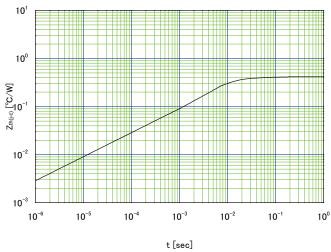
Graph.14 Typical reverse recovery characteristics vs. I_{F} T_j=175°C, V_{cc}=400V, L=500 μ H, V_{cE}=15V,R_c=10 Ω



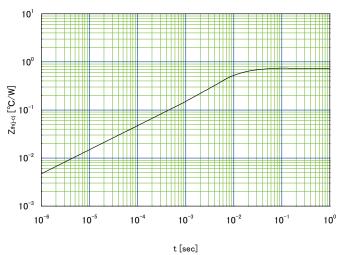
Graph.16 Reverse biased Safe Operating Area $T_1 \le 175^{\circ}C$, $V_{\text{o}\text{E}} = +15 \text{V}/0 \text{V}$, $R_{\text{o}} = 10 \Omega$



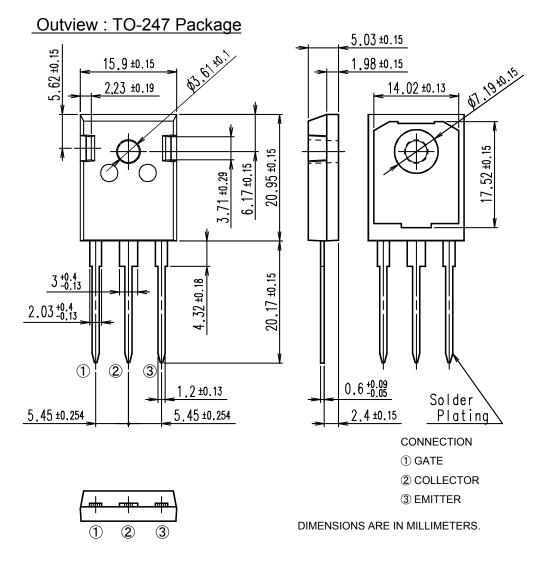
Graph.17
Transient thermal resistance of IGBT



Graph.18
Transient thermal resistance of FWD



■ Outline Drawings, mm



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